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09/636,484

APPLICANT

LIST OF REFERENCES CITED BY APPLICANT

8/10/00

BRADDOCK

FILING DATE

GROUP

08-10-2000

2811

U.S. PATENT DOCUMENTS

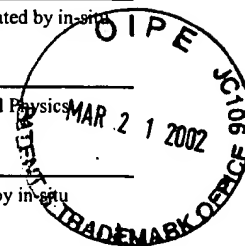
EXAMINER INITIAL		DOCUMENT NUMBER	DATE (Issue)	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
DN	AA	4,416,952	12-1983	Nishizawa	428	698	
DN	AB	4,561,915	12-1985	Mito	148	171	
BNL	AC	4,745,082	5-1998	Kwok	437	39	
BN	AD	4,802,180	1-1989	Brandle Jr. et. al.	372	41	
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GN	AG	4,935,789	6-1990	Calviello	357	22	
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BNL	AN	5,767,388	6-1998	Fleischer et. al.	73	31	
BNL	AO	5,821,171	10-1998	Hong et. al.	438	767	
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BNL	AQ	5,945,718	8-1999	Passlack et. al.	257	410	
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BNL	AX	6,313,511	11-2001	Noguchi	257	392	
	AY						
	AZ						

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					YES	NO
BNL	BA	JP 8085873 A	4-1998	JAPAN, Yoshizawa et. al.	yes	
	BB					
	BC					
	BD					
	BE					
	BF					
	BG					

OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)

DHL	BH	Passlack et. al., "Thermodynamic and photochemical stability of low interface state density Ga ₂ O ₃ -GaAs structures fabricated by in-situ molecular beam epitaxy", Applied Physics Letters, Volume 69, Number 3, pages 302-304, 15 July 1996
DHL	BI	Passlack et. al., " Recombination velocity at oxide-GaAs interfaces fabricated by in-situ molecular beam epitaxy", Applied Physics Letters, Volume 68, Number 25, pages 3605-3607, 17 June 1997
DHL	BJ	Passlack et. al. "Quasistatic and high frequency capacitance-vltage characterization of Ga ₂ O ₃ -GaAs structures fabricated by in-situ molecular beam epitaxy", Applied Physics Letters, Volume 68, Number 8, pages 1099-1101, 19 February 1996
bhl	BK	Ueda et. al. "Anisotropy of electrical and optical properties in B-Ga ₂ O ₃ single crystals", Applied Physics Letters, Volume 71, Number 7, Pages 933-935, 18 August 1997
DHL	BL	Ueda et. al. "Synthesis and control of conductivity of ultraviolet transmitting B-Ga ₂ O ₃ single crystals", Applied Physics Letters, Volume 70, Number 26, pages 3561-3563, 30 June 1997



Examiner Donghee Kang Date Considered 6-28-02

*Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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